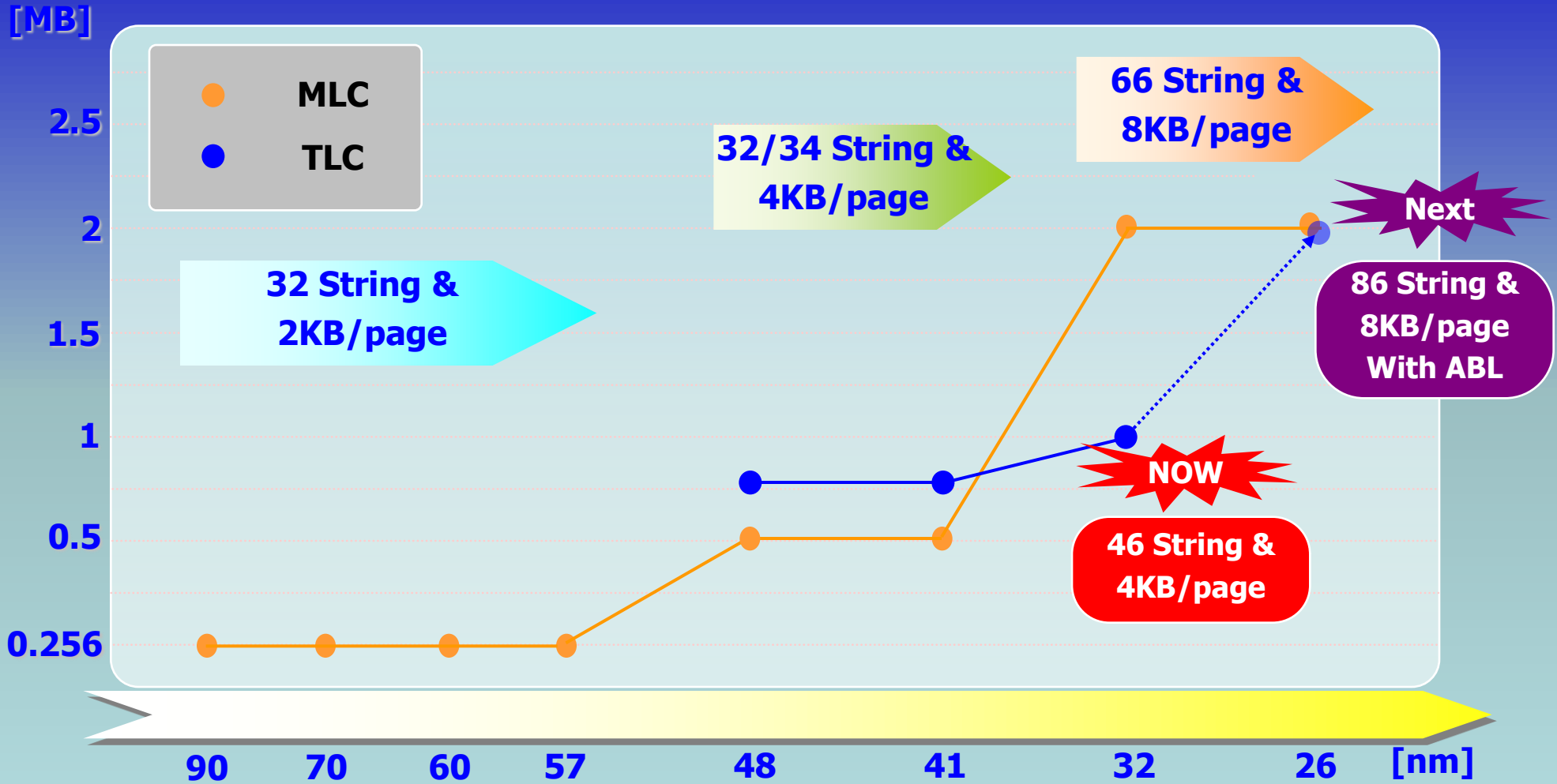


Consideration for Determining Page/Block Size in NAND Flash

**Hynix Semiconductor Inc.
Apr. 19, 2010**

Hynix NAND Block Size Trend



Factor of the Increasing Page/Block Size

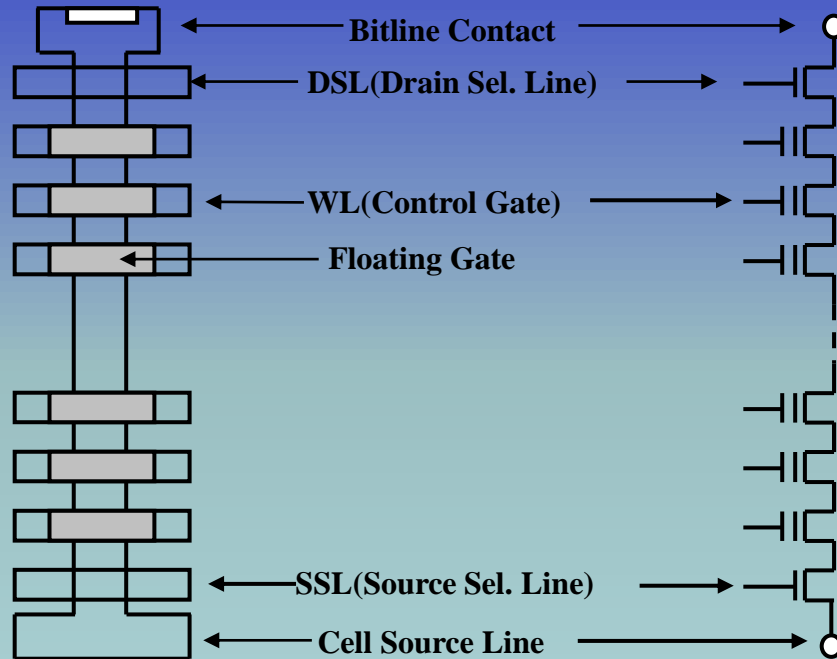
$$\begin{aligned}\text{Block Size} &= \text{page num} * \text{page size} \\ &= (\text{bit / cell}) * \text{string num} * \text{E/O} * \text{page size}\end{aligned}$$

Item	Trend	Characteristics
Bit / cell	SLC → MLC → TLC	+) bit growth ↑ -) tPROG/tR/Reliability ↓
String	32 string → 64 string	+) bit growth ↑ -) disturbance ↑
Page size	2KB → 4KB → 8KB	+) performance ↑ -) chip size ↑
Bit Line	EOBL → ABL	+) block size ↓ -)

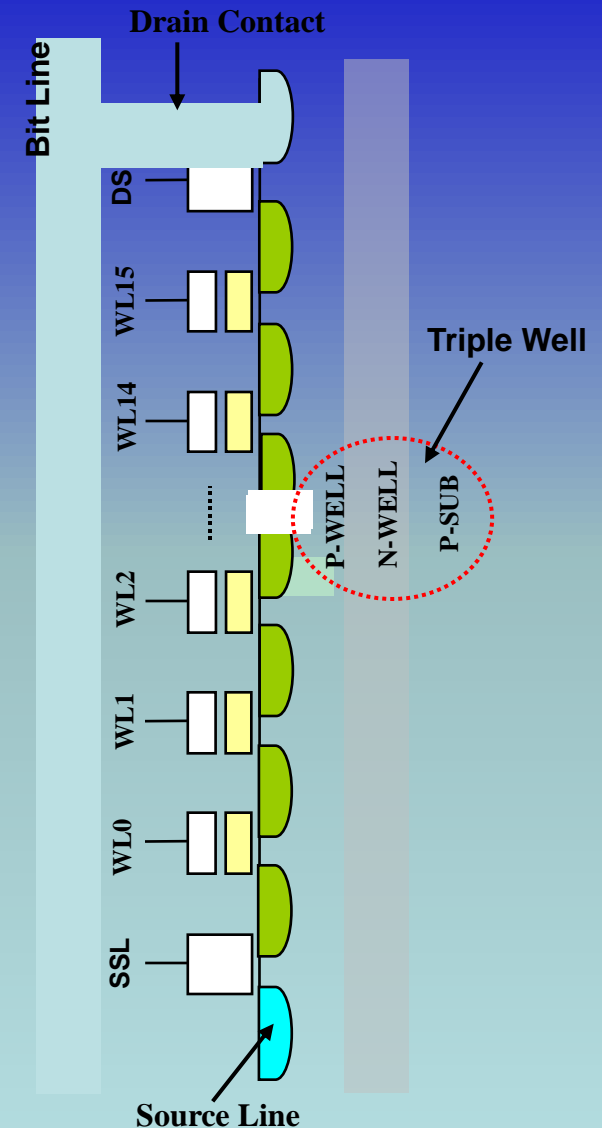
Architecture & Specification

- What's a cell string?

; Cell Operation Unit of Read/Program

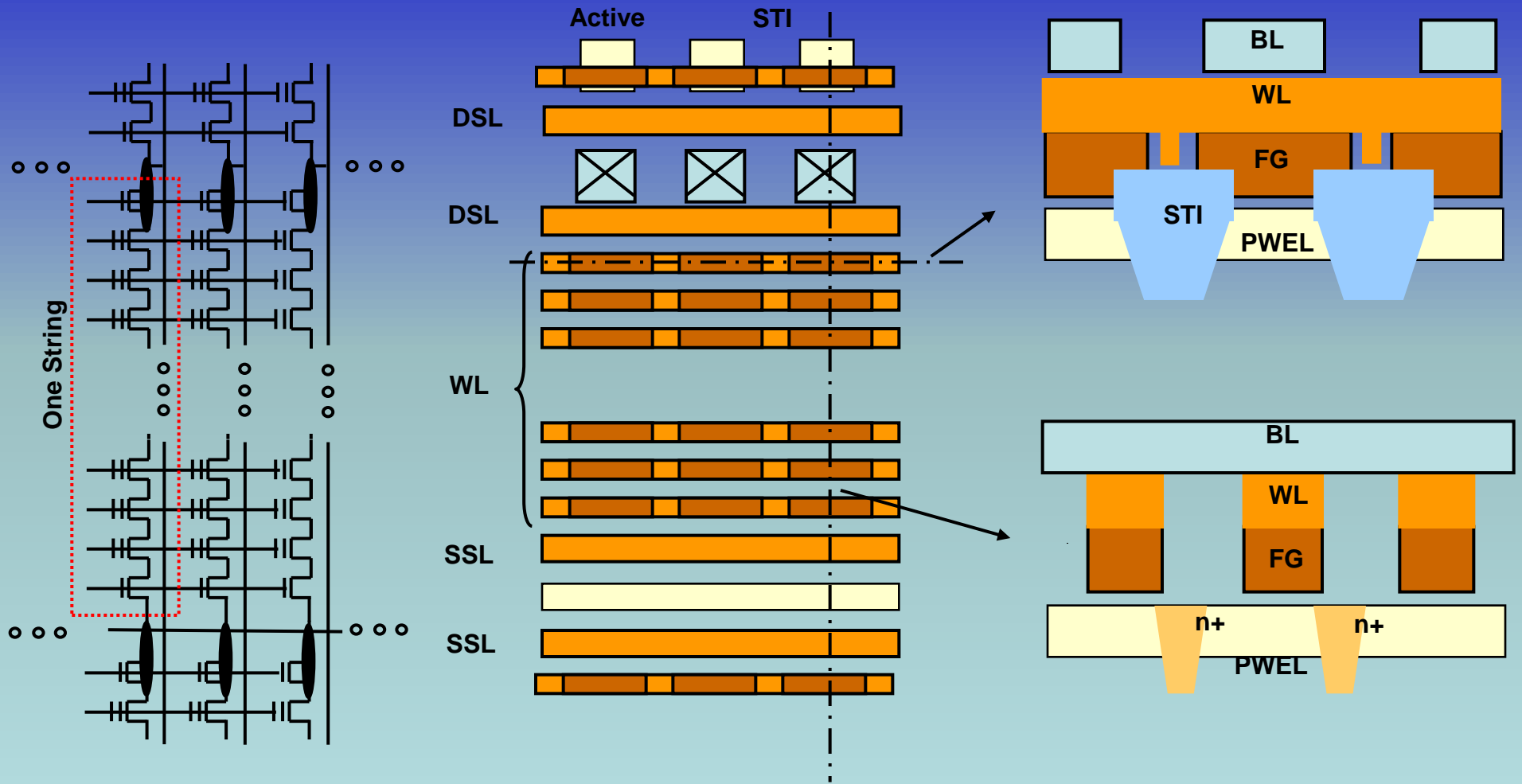


Tech.	0.12um	0.09um	0.07um
String	16	32	32
Density	512M, 1G	512M, 1G, 2G	1G, 2G, 4G



Architecture & Specification

- NAND Cell Array



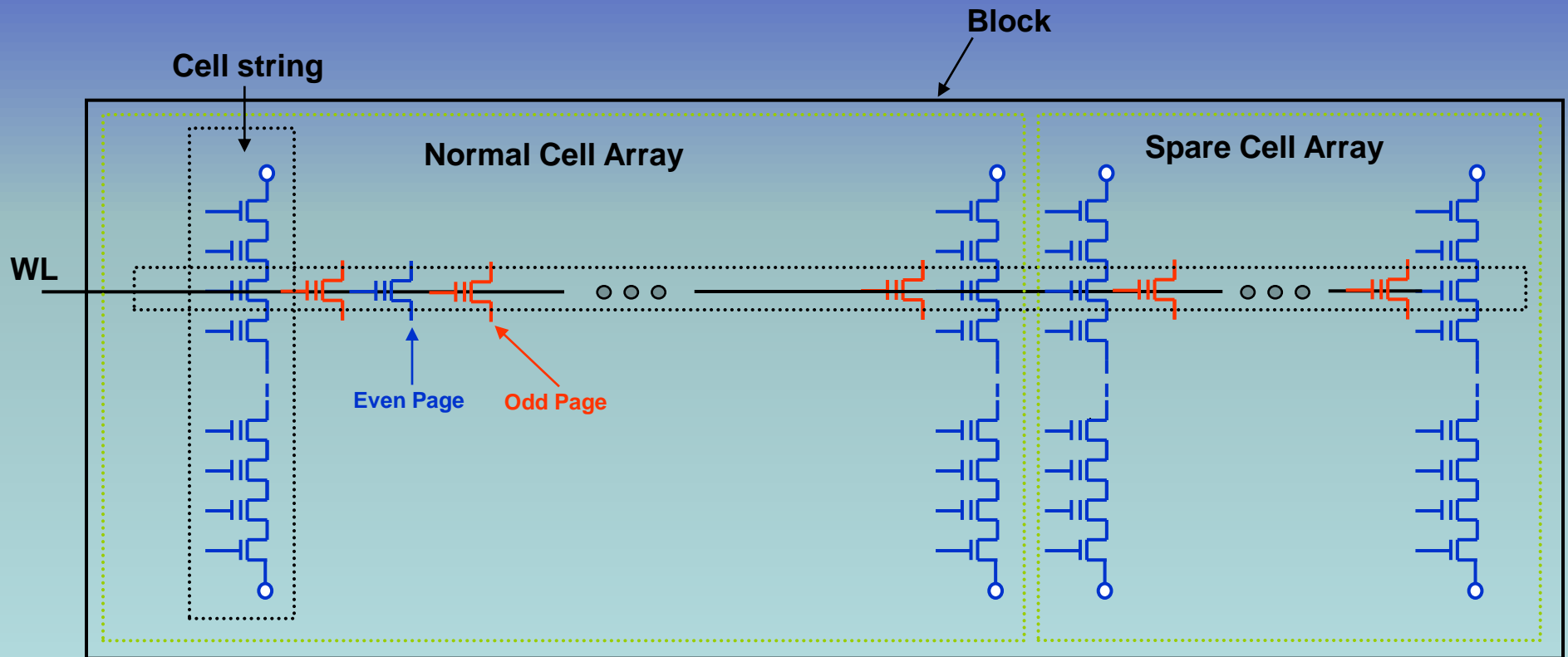
Architecture & Specification

- Page & Block

- Cell Array = Normal cell + Spare cell

- What's a cell string, a page and a block ?

- One word line = Even page + Odd page



Thank You